



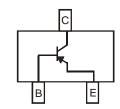
LOW $V_{CE(SAT)}$ PNP SURFACE MOUNT TRANSISTOR

Features

- Epitaxial Planar Die Construction
- Low Collector-Emitter Saturation Voltage
- Ideal for Low Power Amplification and Switching
- Complementary NPN Type Available (2DD2656)
- Ultra-Small Surface Mount Package
- Lead Free By Design/RoHS Compliant (Note 1)
- "Green Device" (Note 2)

Mechanical Data

- Case: SOT-323
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020D
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
 Solderable per MIL-STD-202, Method 208
- Terminal Connections: See Diagram
- Marking Information: See Page 3
- Ordering Information: See Page 3
- Weight: 0.006 grams (approximate)



Device Schematic



Top View

Maximum Ratings @T_A = 25°C unless otherwise specified

| Characteristic | Symbol | Value | Unit |
|--------------------------------|------------------|-------|------|
| Collector-Base Voltage | V _{CBO} | -30 | V |
| Collector-Emitter Voltage | V _{CEO} | -30 | V |
| Emitter-Base Voltage | V _{EBO} | -6 | V |
| Collector Current - Continuous | Ic | -1 | А |
| Peak Pulse Collector Current | I _{CM} | -2 | Α |

Thermal Characteristics

| Characteristic | Symbol | Value | Unit |
|--|-----------------------------------|-------------|------|
| Power Dissipation (Note 3) @ T _A = 25°C | P_{D} | 300 | mW |
| Thermal Resistance, Junction to Ambient (Note 3) @ T _A = 25°C | $R_{	hetaJA}$ | 417 | °C/W |
| Power Dissipation (Note 4) @ T _A = 25°C | P_{D} | 500 | mW |
| Thermal Resistance, Junction to Ambient (Note 4) @ T _A = 25°C | $R_{	hetaJA}$ | 250 | °C/W |
| Operating and Storage Temperature Range | T _J , T _{STG} | -55 to +150 | °C |

Electrical Characteristics @TA = 25°C unless otherwise specified

| Characteristic | Symbol | Min | Тур | Max | Unit | Conditions |
|--|----------------------|-----|------|------|------|---|
| OFF CHARACTERISTICS | | | | | | |
| Collector-Base Breakdown Voltage | V _{(BR)CBO} | -30 | _ | _ | V | $I_C = -10\mu A, I_E = 0$ |
| Collector-Emitter Breakdown Voltage (Note 5) | V _{(BR)CEO} | -30 | _ | _ | V | $I_C = -1 \text{mA}, I_B = 0$ |
| Emitter-Base Breakdown Voltage | $V_{(BR)EBO}$ | -6 | _ | _ | V | $I_E = -10\mu A, I_C = 0$ |
| Collector Cut-Off Current | I _{CBO} | _ | _ | -0.1 | μА | V _{CB} = -30V, I _E = 0 |
| Emitter Cut-Off Current | | _ | _ | -0.1 | μΑ | $V_{EB} = -6V, I_{C} = 0$ |
| ON CHARACTERISTICS (Note 5) | | | • | | | • |
| Collector-Emitter Saturation Voltage | V _{CE(SAT)} | _ | -180 | -380 | mV | $I_C = -500 \text{mA}, I_B = -25 \text{mA}$ |
| DC Current Gain | h _{FE} | 270 | _ | 680 | _ | $V_{CE} = -2V, I_{C} = -100 \text{mA}$ |
| SMALL SIGNAL CHARACTERISTICS | | | | | | |
| Output Capacitance | C _{obo} | _ | 16 | _ | pF | $V_{CB} = -10V, I_{E} = 0,$ f = 1MHz |
| Current Gain-Bandwidth Product | f⊤ | _ | 300 | _ | MHz | $V_{CE} = -2V, I_{C} = -100 \text{mA},$ f = 100MHz |

Notes:

- 1. No purposefully added lead.
- 2. Diode's Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.
- 3. Device mounted on FR-4 PCB with minimum recommended pad layout.
- Device mounted on FR-4 PCB with 1 inch² copper pad layout.
- Measured under pulsed conditions. Pulse width = 300 μs. Duty cycle ≤2%.



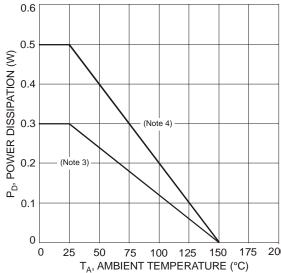
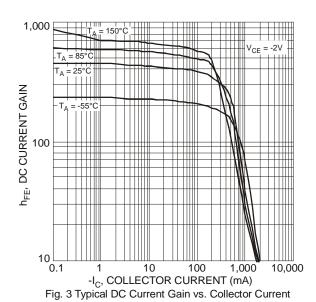
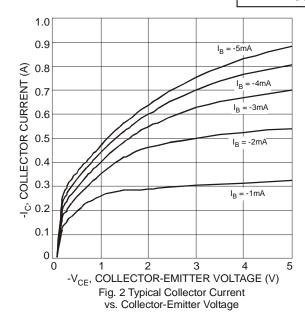


Fig. 1 Power Dissipation vs. Ambient Temperature





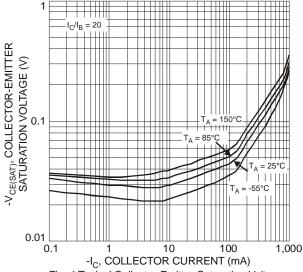


Fig. 4 Typical Collector-Emitter Saturation Voltage vs. Collector Current

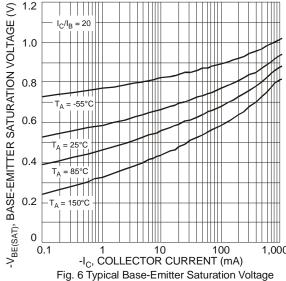
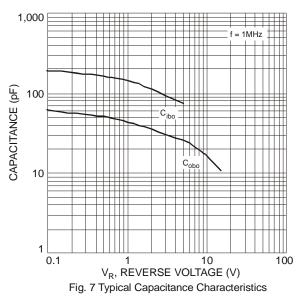


Fig. 6 Typical Base-Emitter Saturation Voltage vs. Collector Current



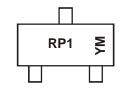


Ordering Information (Note 6)

| Part Number | Case | Packaging |
|-------------|---------|------------------|
| 2DB1694-7 | SOT-323 | 3000/Tape & Reel |

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

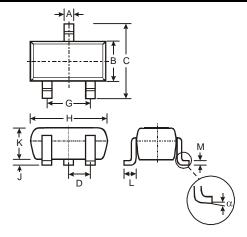


RP1 = Product Type Marking Code YM = Date Code Marking Y = Year (ex: V = 2008) M = Month (ex: 9 = September)

Date Code Key

| Year | 2008 | | 2009 | 2010 | | 2011 | 2012 | | 2013 | 2014 | | 2015 |
|-------|------|-----|------|------|-----|------|------|-----|------|------|-----|------|
| Code | V | | W | X | | Υ | Z | | Α | В | | С |
| Month | Jan | Feb | Mar | Apr | May | Jun | Jul | Aug | Sep | Oct | Nov | Dec |
| Code | 1 | 2 | 3 | 4 | 5 | 6 | 7 | 8 | 9 | 0 | N | D |

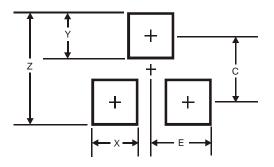
Package Outline Dimensions



| SOT-323 | | | | | | |
|---------|----------------------|------|------|--|--|--|
| Dim | Min | Max | Тур | | | |
| Α | 0.25 | 0.40 | 0.30 | | | |
| В | 1.15 | 1.35 | 1.30 | | | |
| С | 2.00 | 2.20 | 2.10 | | | |
| D | - | - | 0.65 | | | |
| G | 1.20 | 1.40 | 1.30 | | | |
| Н | 1.80 | 2.20 | 2.15 | | | |
| J | 0.0 | 0.10 | 0.05 | | | |
| K | 0.90 | 1.00 | 1.00 | | | |
| L | 0.25 | 0.40 | 0.30 | | | |
| М | 0.10 | 0.18 | 0.11 | | | |
| α | 0° | 8° | - | | | |
| All | All Dimensions in mm | | | | | |



Suggested Pad Layout



| Dimensions | Value (in mm) |
|------------|---------------|
| Z | 2.8 |
| Х | 0.7 |
| Υ | 0.9 |
| С | 1.9 |
| E | 1.0 |

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Document number: DS31640 Rev. 2 - 2

单击下面可查看定价,库存,交付和生命周期等信息

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